

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

BFL4004 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)= 1.9Ω (typ.)
- 10V drive
- Input capacitance Ciss=710pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		800	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	6.5	А
	IDpack*2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	4.3	Α
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	13	Α
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	36	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		225	mJ
Avalanche Current *5	I _{AV}		6.5	Α

Note:*1 Shows chip capability

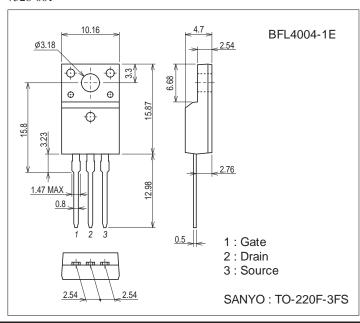
- *2 Package limited
- *3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=50V, L=10mH, IAV=6.5A (Fig.1)
- *5 L≤10mH, single pulse

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

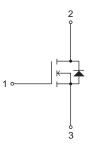
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./tube

Marking Electrical Connection





SANYO Semiconductor Co., Ltd.

http://www.sanyosemi.com/en/network/

Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	800			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =640V, V _{GS} =0V			1.0	mA	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		4.0	V	
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =3.25A	1.7	3.4		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =3.25A, V _G S=10V		1.9	2.5	Ω	
Input Capacitance	Ciss			710		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		120		pF	
Reverse Transfer Capacitance	Crss			42		pF	
Turn-ON Delay Time	t _d (on)			17		ns	
Rise Time	t _r	San Fig 2		44		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		130		ns	
Fall Time	tf			44		ns	
Total Gate Charge	Qg			36		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		6.2		nC	
Gate-to-Drain "Miller" Charge	Qgd			18		nC	
Diode Forward Voltage	V _{SD}	I _S =6.5A, V _G S=0V		0.85	1.2	V	
Reverse Recovery Time	t _{rr}	See Fig.3		970		ns	
Reverse Recovery Charge	Q _{rr}	IS=6.5A, VGS=0V, di/dt=100A/μs		6700		nC	

Fig.1 Unclamped Inductive Switching Test Circuit

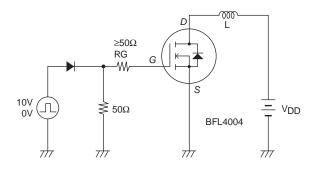


Fig.3 Reverse Recovery Time Test Circuit

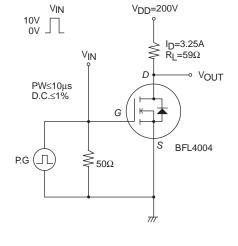
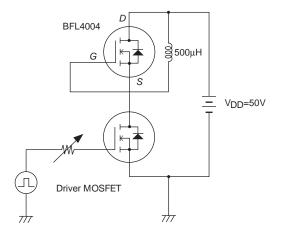
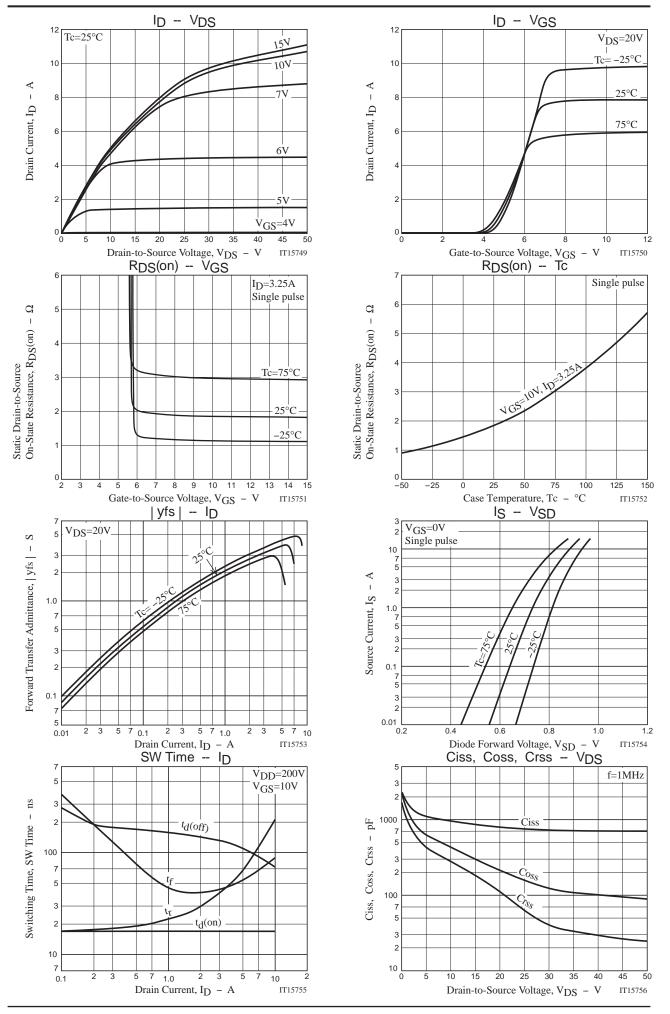


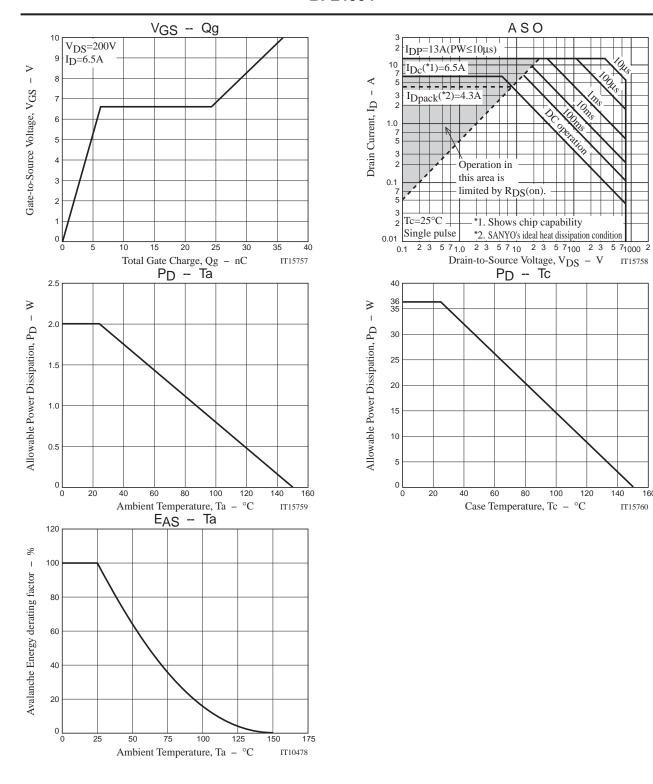
Fig.2 Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
BFL4004-1E	TO-220F-3FS	50pcs./tube	Pb Free





140

160

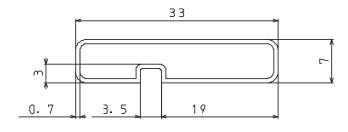
IT15760

Magazine Specification

BFL4004-1E

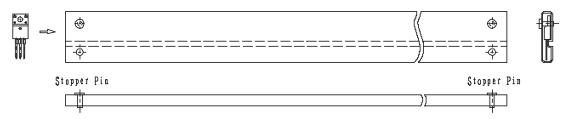
1. Packing Format

Package Name	Magazine Name	I 4.55 to		Maximum Number of devices contained (pcs)			Packing format		
1 4 4 4 4 4 1 4 4 4 4	Idag as the Hams	l	Inner box	Outer box	Inner BOX	Outer BOX			
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178			



Tolerance=±0.3mm
Thickness=0.7±0,2mm
Length =532.5±2mm
Material =PVC (Antistatic treatment)

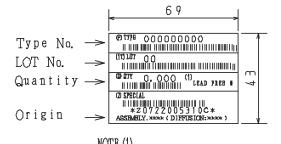
3. Storage method to magazine

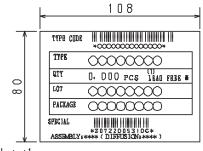


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shigments. The form of a label may change in physical distribution process.



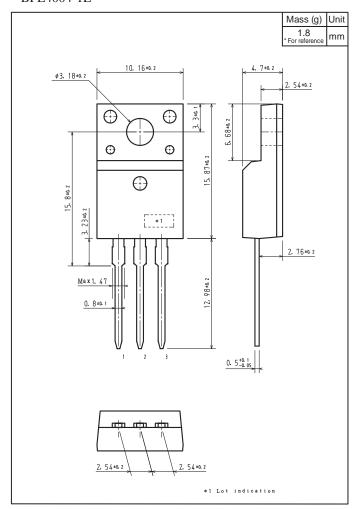


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

BFL4004-1E



Note on usage: Since the BFL4004 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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